

N-Channel Enhancement Mode Power MOSFET

Description

The HM30N10K uses advanced trench technology and design to provide excellent $R_{DS(ON)}$ with low gate charge. It can be used in a wide variety of applications.

General Features

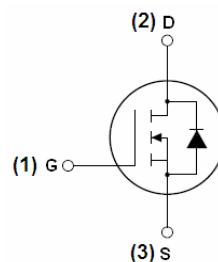
- $V_{DS} = 100V, I_D = 30A$
 $R_{DS(ON)} < 31m\Omega @ V_{GS}=10V$ (Typ:27m Ω)
- Special process technology for high ESD capability
- High density cell design for ultra low R_{dson}
- Fully characterized avalanche voltage and current
- Good stability and uniformity with high E_{AS}
- Excellent package for good heat dissipation

Application

- Power switching application
- Hard switched and high frequency circuits
- Uninterruptible power supply

100% UIS TESTED!

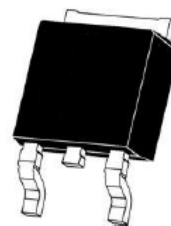
100% ΔV_{ds} TESTED!



Schematic diagram



Marking and pin assignment



TO-252 -2Ltop view

Package Marking and Ordering Information

Device Marking	Device	Device Package	Reel Size	Tape width	Quantity
HM30N10K	HM30N10K	TO-252-2L	-	-	-

Absolute Maximum Ratings ($T_c=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage	100	V
V_{GS}	Gate-Source Voltage	± 20	V
I_D	Drain Current-Continuous	30	A
$I_D (100^\circ\text{C})$	Drain Current-Continuous($T_C=100^\circ\text{C}$)	21	A
I_{DM}	Pulsed Drain Current	90	A
P_D	Maximum Power Dissipation	85	W
	Derating factor	0.57	W/ $^\circ\text{C}$
E_{AS}	Single pulse avalanche energy ^(Note 5)	256	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	$^\circ\text{C}$

Thermal Characteristic

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case ^(Note 2)	1.8	°C/W
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Electrical Characteristics ($T_c=25^{\circ}\text{C}$ unless otherwise noted)

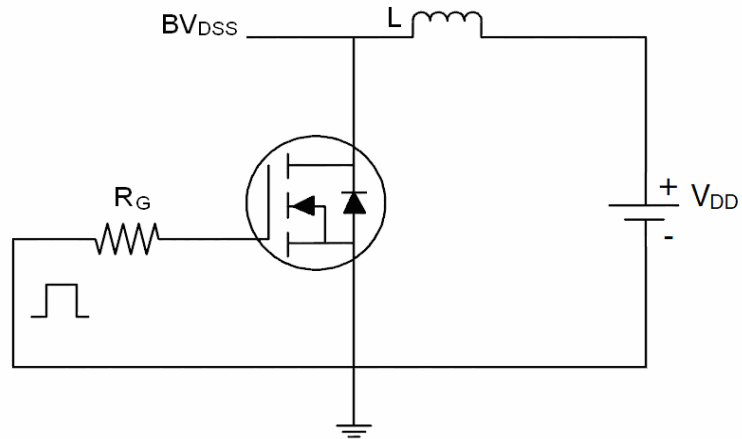
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V I _D =250μA	100	115	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =100V, V _{GS} =0V	-	-	1	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
On Characteristics ^(Note 3)						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.3	1.9	2.5	V
R _{DS(ON)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =10A	-	27	31	mΩ
g _{FS}	Forward Transconductance	V _{DS} =5V, I _D =10A	-	15	-	S
Dynamic Characteristics ^(Note4)						
C _{iss}	Input Capacitance	V _{DS} =25V, V _{GS} =0V, F=1.0MHz	-	2000	-	PF
C _{oss}	Output Capacitance		-	300	-	PF
C _{rss}	Reverse Transfer Capacitance		-	250	-	PF
Switching Characteristics ^(Note 4)						
t _{d(on)}	Turn-on Delay Time	V _{DD} =50V, R _L =5Ω V _{GS} =10V, R _{GEN} =3Ω	-	7	-	nS
t _r	Turn-on Rise Time		-	7	-	nS
t _{d(off)}	Turn-Off Delay Time		-	29	-	nS
t _f	Turn-Off Fall Time		-	7	-	nS
Q _g	Total Gate Charge	V _{DS} =50V, I _D =10A, V _{GS} =10V	-	39	-	nC
Q _{gs}	Gate-Source Charge		-	8	-	nC
Q _{gd}	Gate-Drain Charge		-	12	-	nC
Drain-Source Diode Characteristics						
V _{SD}	Diode Forward Voltage ^(Note 3)	V _{GS} =0V, I _S =10A	-	-	1.2	V
I _S	Diode Forward Current ^(Note 2)	-	-	-	30	A
t _{rr}	Reverse Recovery Time	T _J = 25°C, I _F = 10A	-	32	-	nS
Q _{rr}	Reverse Recovery Charge	di/dt = 100A/μs ^(Note3)	-	53	-	nC
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible (turn-on is dominated by LS+LD)				

Notes:

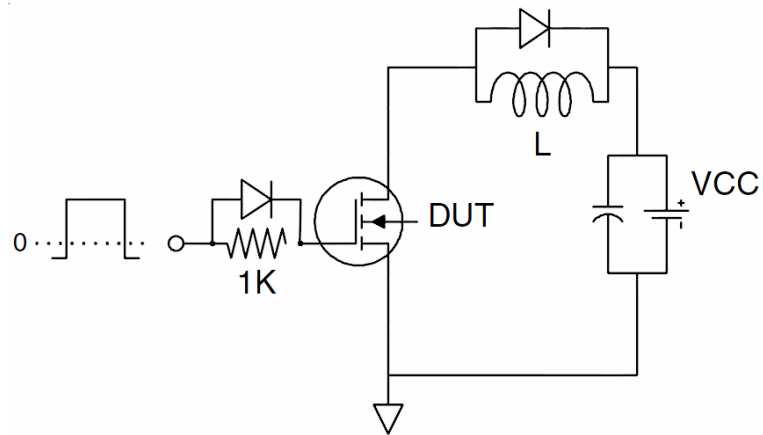
1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS Condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega, I_{AS}=32A$

Test Circuit

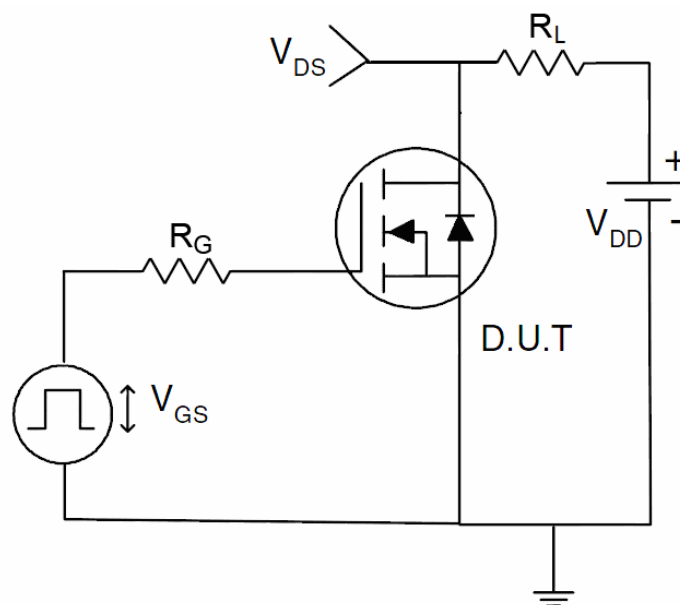
1) E_{AS} Test Circuit



2) Gate Charge Test Circuit



3) Switch Time Test Circuit



Typical Electrical and Thermal Characteristics (Curves)

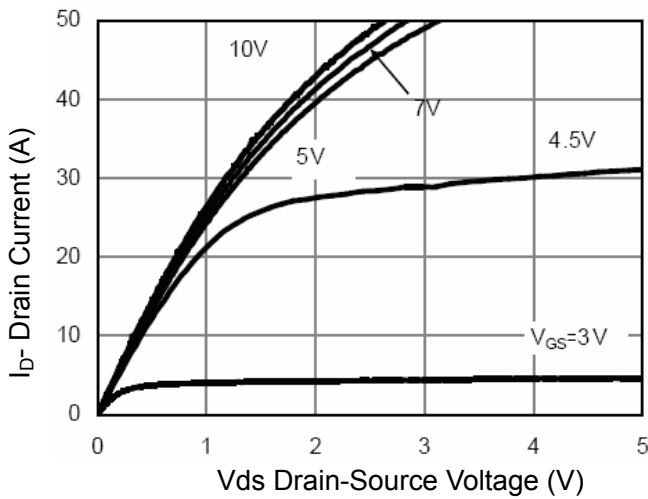


Figure 1 Output Characteristics

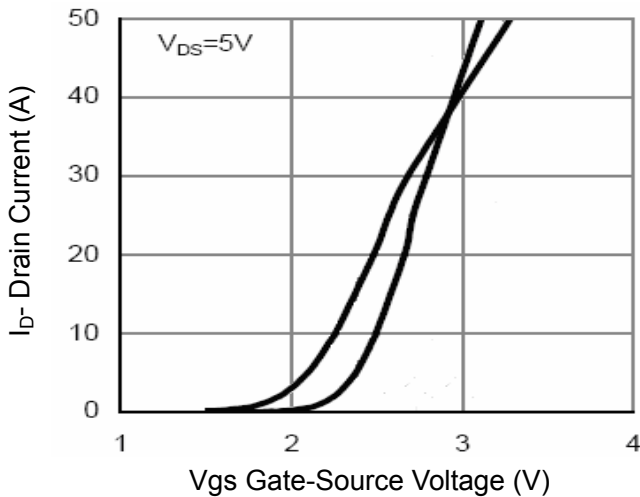


Figure 2 Transfer Characteristics

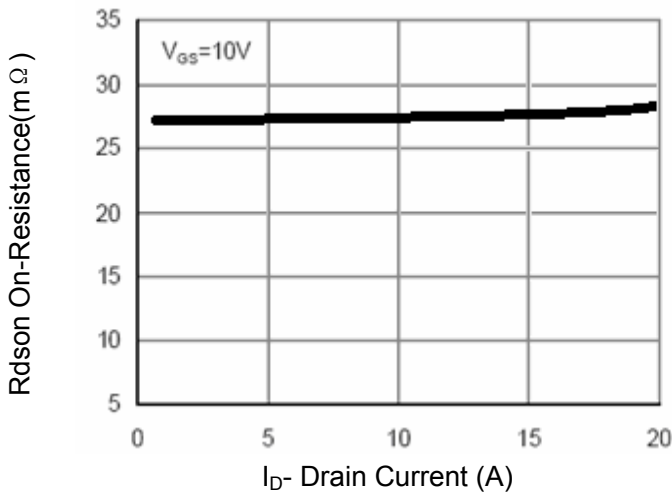


Figure 3 $R_{DS(on)}$ - Drain Current

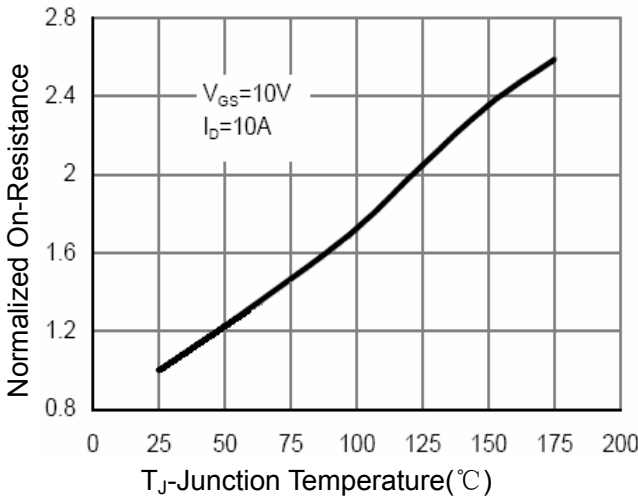


Figure 4 $R_{DS(on)}$ -Junction Temperature

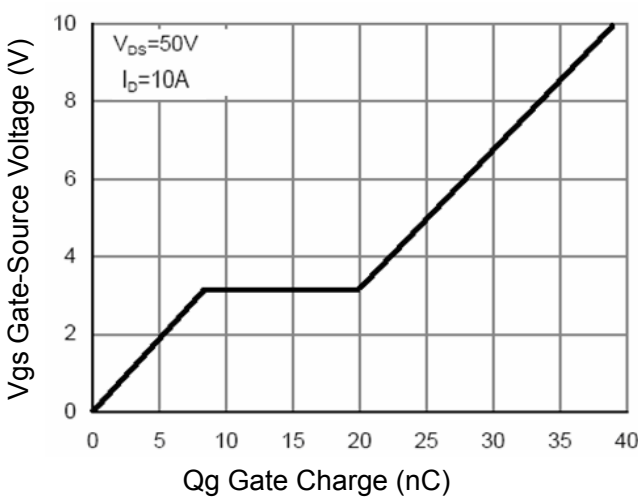


Figure 5 Gate Charge

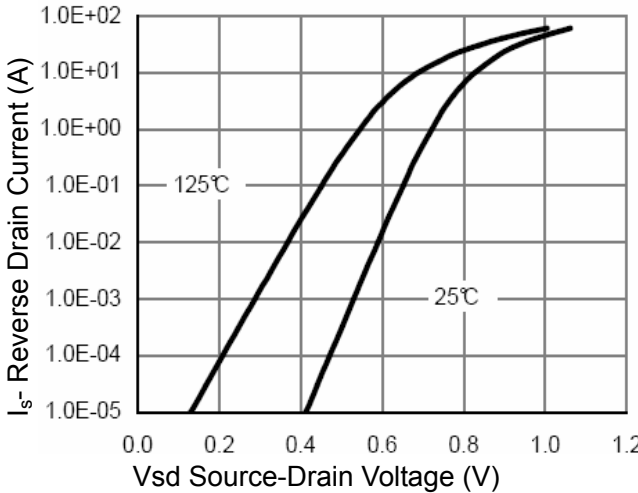


Figure 6 Source- Drain Diode Forward

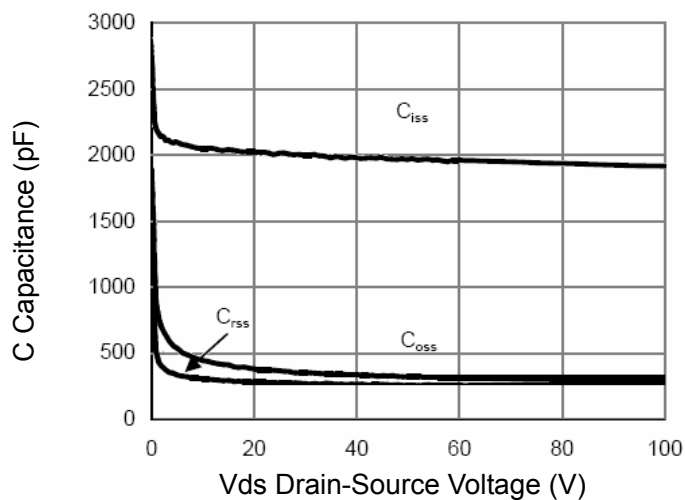


Figure 7 Capacitance vs Vds

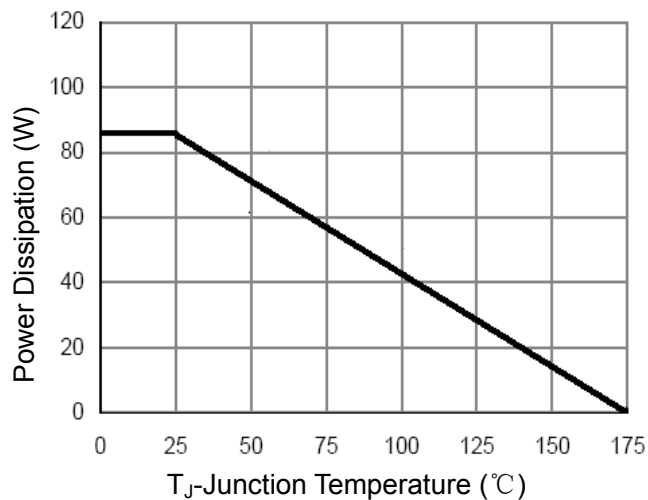


Figure 9 Power De-rating

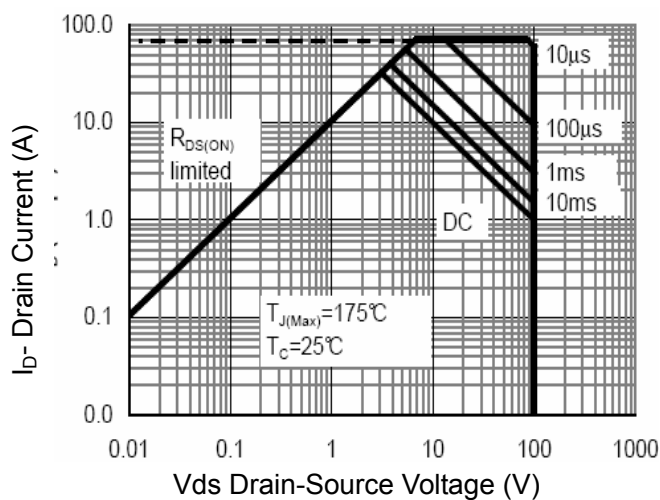


Figure 8 Safe Operation Area

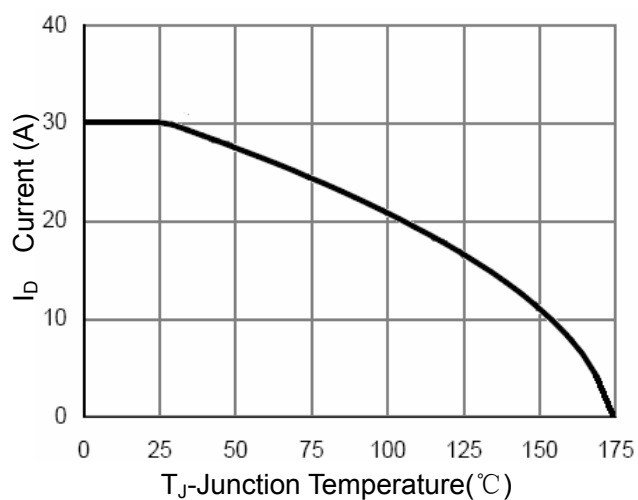


Figure 10 ID Current- Junction Temperature

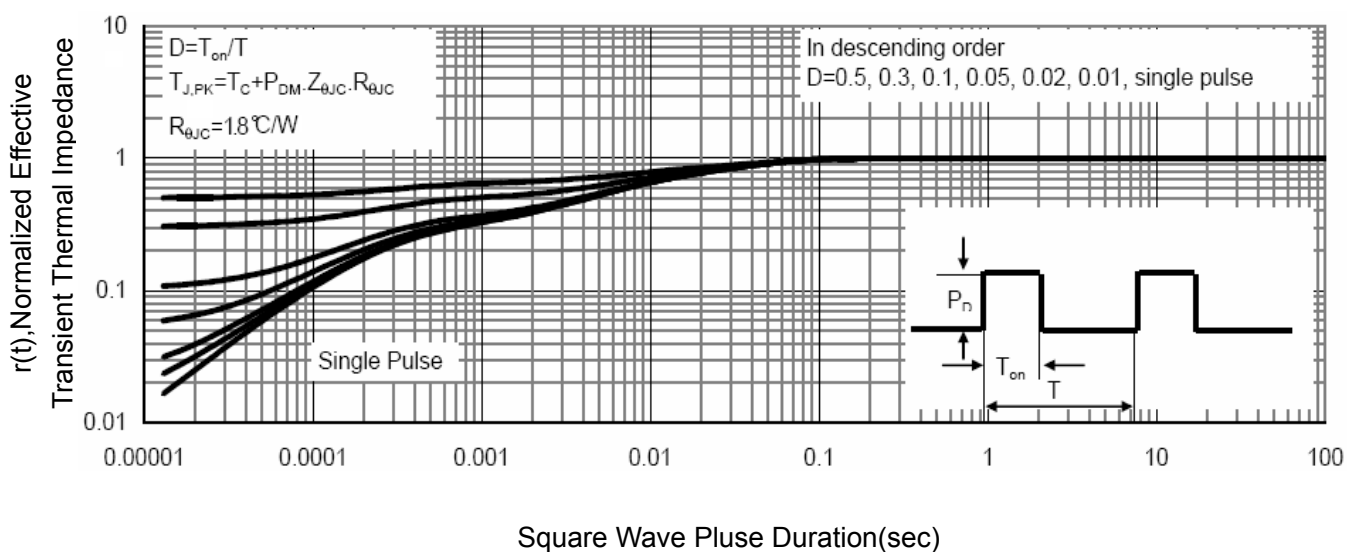
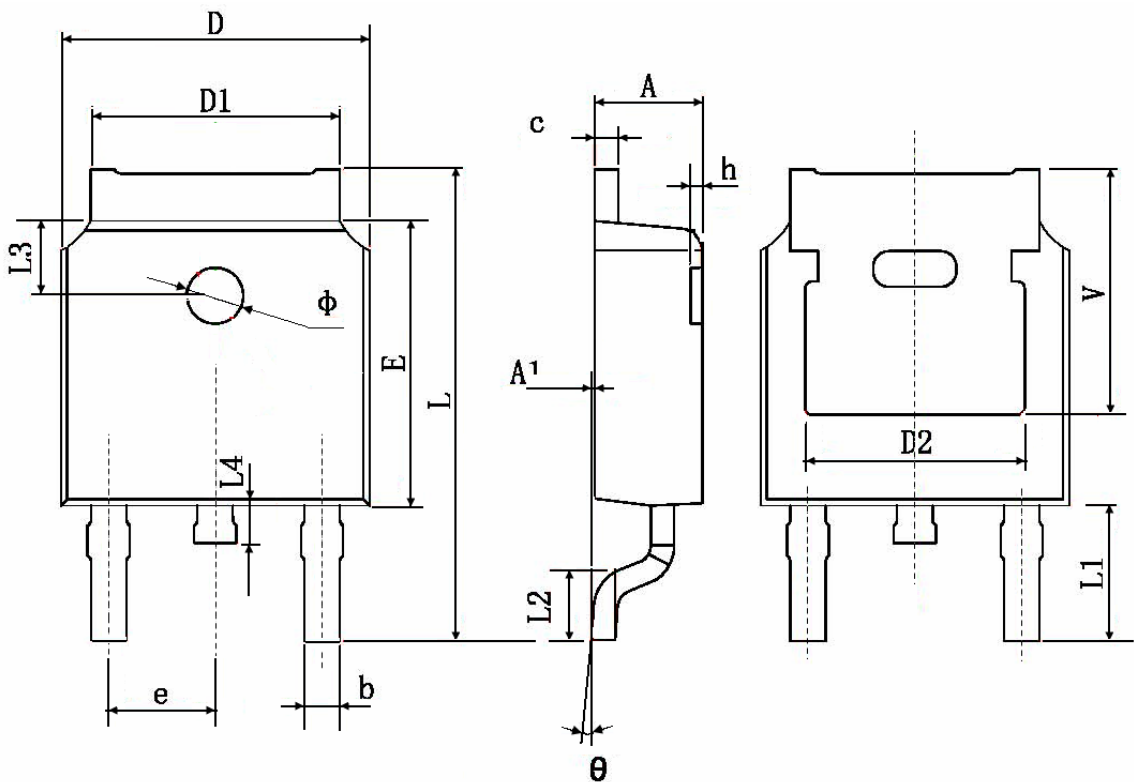


Figure 11 Normalized Maximum Transient Thermal Impedance

TO-252 Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
b	0.660	0.860	0.026	0.034
c	0.460	0.580	0.018	0.023
D	6.500	6.700	0.256	0.264
D1	5.100	5.460	0.201	0.215
D2	4.830 TYP.		0.190 TYP.	
E	6.000	6.200	0.236	0.244
e	2.186	2.386	0.086	0.094
L	9.800	10.400	0.386	0.409
L1	2.900 TYP.		0.114 TYP.	
L2	1.400	1.700	0.055	0.067
L3	1.600 TYP.		0.063 TYP.	
L4	0.600	1.000	0.024	0.039
Φ	1.100	1.300	0.043	0.051
θ	0°	8°	0°	8°
h	0.000	0.300	0.000	0.012
V	5.350 TYP.		0.211 TYP.	